FORM PTO-1449 (SUBSTITUTE)  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))					Attorney Docket No.: P2001,0176 Appl. No.:  Applicant: JOHANNES BAUR ET AL.  Filing Date: September 9, 2003 Group Art Unit:					
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